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C, 60. A physical vapor deposition target comprising an alloy of copper and one or more other elements, the one or more other elements being present in the alloy at a total concentration from less than 1.0 at% to 0.001 at% and being selected from the group consisting of Sr, Ba, Sc, and Se.

61. The physical vapor deposition target of claim 60 wherein the one or more other elements are present in the alloy at a total concentration at from 0.005 at% to 0.1 at%.

62. The physical vapor deposition target of claim 60 comprising an RF sputtering coil.

63. The physical vapor deposition target of claim 60 wherein the element comprises Sr.

64. The physical vapor deposition target of claim 60 wherein the element comprises Ba.

65. The physical vapor deposition target of claim 60 wherein the element comprises Sc.

66. The physical vapor deposition target of claim 60 wherein the element comprises Se.

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67. (New) The physical vapor deposition target of claim 60 wherein the one or more other elements are present in the alloy as uniformly distributed fine precipitates in the alloy microstructure.

68. (New) The physical vapor deposition target of claim 60 wherein the average grain size is less than or equal to about 20 micrometers.

69. (New) A physical vapor deposition target comprising a copper alloy, the alloy consisting of copper having a purity of 99.9998% alloyed with a total concentration of other elements of from less than 1.0 at% to 0.001 at%, the other elements being selected from the group consisting of Sr, Ba, Sc, and Se.

70. (New) The physical vapor deposition target of claim 69 wherein the copper alloy comprises an average grain size and comprises an electromigration resistance higher than the electromigration resistance of copper having a purity of greater than 99.999% of the same average grain size.

71. (New) The physical vapor deposition target of claim 69 wherein the copper alloy comprises an average grain size and comprises a thermal stability to grain size retention that is higher than the thermal stability to grain size retention of copper having a purity of greater than 99.999% of the same average grain size.

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72. (New) The physical vapor deposition target of claim 69 comprising three or fewer of the other elements.

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